
CHAPTER 3

Study of structural, compositional and optical properties of MoS₂, WS₂ and ternary compound MoW-disulfide NPs

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The detailed analysis of various characterization results of ternary compound disulfides of Mo and W have been discussed in this chapter. Differences in optical properties of such TMD NPs and differences in their structure have been investigated and reported in this chapter. The structural and optical properties of our as-synthesized MoS₂ and WS₂ NPs and ternary disulfides of Mo and W, namely MoW-disulfide1 and MoW-disulfide2 were reported and compared the findings with existing literature. The chapter is mainly divided into four sections. Section 3.1 deals in the structural and optical properties of MoS₂ NPs, section 3.2 deals in the structural and optical properties of WS₂ NPs, section 3.3 deals in the structural and optical properties of the ternary compound MoW-disulfide NPs and section 3.4 deals in the photoluminescent behavior of the as-synthesized NPs. Experimental observations reveal that the structural behavior remains intact in the as-synthesized ternary TMD NPs like that of MoS₂ and WS₂ NPs, however, there is slight modification due to the formation of new bonds in the ternary compounds. There are some interesting changes in the optical properties of the ternary compounds as well which leads to enhancement in the luminescence and photocatalytic behavior of the as-synthesized compound disulfides. The structural and optical characterization of the as-synthesized MoS₂, WS₂ and compound MoW-disulfide NPs are discussed in the following sections.

3.1 Structural and optical properties of MoS₂ NPs

3.1.1 Structural characterizations of MoS₂ NPs

The morphology of the as-synthesized MoS₂ NPs were studied by using different analytic techniques such as XRD, TEM, SEM, Raman spectroscopy etc. Compositional analysis was performed by using EDS and elemental mapping was obtained with SEM.

Figure 3.1 is the XRD pattern of MoS₂ NPs obtained from X-ray Diffractometer (make: RIGAKU MINIFLEX) with Cu-K α radiation ($\lambda= 1.5405 \text{ \AA}$) in the 2θ range from 10° to 70° . For the MoS₂ sample XRD peaks at 2θ equal to 14.24° , 28.36° , 33.01° , 35.83° , 42.98° , 58.71° , 58.90° correspond to the Millar crystal planes (002), (004), (100), (102), (006), (110), (008) respectively when compared with JCPDS software having file No. 75-1539 (PCPDFWIN v.2.02). These Millar planes correspond to the system having hexagonal

symmetry (SG:p6₃/mmc) in MoS₂ lattice. The broadening nature of the XRD peaks is a sign of the smaller crystallite size of the MoS₂ NPs. Also, the XRD pattern reveals that the material is polycrystalline in nature. The crystallite size (L) is calculated using Debye-Scherrer formula 3.1 [1].

$$L = \frac{C_2 \lambda}{\beta \cos\theta} \quad (3.1)$$

where λ , β and θ are the wavelength of X-ray, full width at half maximum (F.W.H.M.) (in radian) of XRD-peak and corresponding Bragg's angle of diffraction peak respectively and C_2 is a constant depending on the assumption made in the theory (in most cases always close to unity and taken to be 0.91). Using relation 3.1 the average crystallite size of the synthesized MoS₂ NPs was calculated to be approximately 11.07 nm.

The simulated powdered XRD (PXRD) pattern for MoS₂ sample in comparison with the experimentally obtained XRD pattern was also plotted in figure 3.1(b). The simulation was done by using the standard software VESTA 3(Visualization for Electronic and SStructural Analysis, version 3) [2]. It is obvious that experimentally synthesized materials have impurities and show deviations, but our experimental XRD plots for MoS₂ shows similarity with the simulated one to a great extent as shown in figure 3.1(b).

TEM analysis was performed to obtain the structural information. The TEM micrograph in figure 3.2(a) shows different crystal planes present in the as-prepared MoS₂ sample. From the crystal planes observed in TEM micrograph, the interplanar spacing 0.63nm and 0.31nm, shown in figure 3.2(a), were determined. These corresponded to the Millar plane (002) and (004) respectively in the MoS₂ crystal. The selected area electron diffraction (SAED) pattern, shown in figure 3.2(c), which was also obtained from TEM confirmed that the as-synthesized MoS₂ NPs were polycrystalline in nature. Figure 3.2(b) shows different grains of MoS₂ NPs.

SEM image having 10,000x magnification of the as-prepared MoS₂ NPs was also obtained. The SEM image is shown in figure 3.3(a). From the SEM micrograph in figure 3.3(a) it was observed that the average particle size for MoS₂ was 62.47nm. The particle size distribution histogram of the as-synthesized materials was evaluated from SEM micrographs and is shown in figure 3.3(b). However, being NPs, due to the high surface

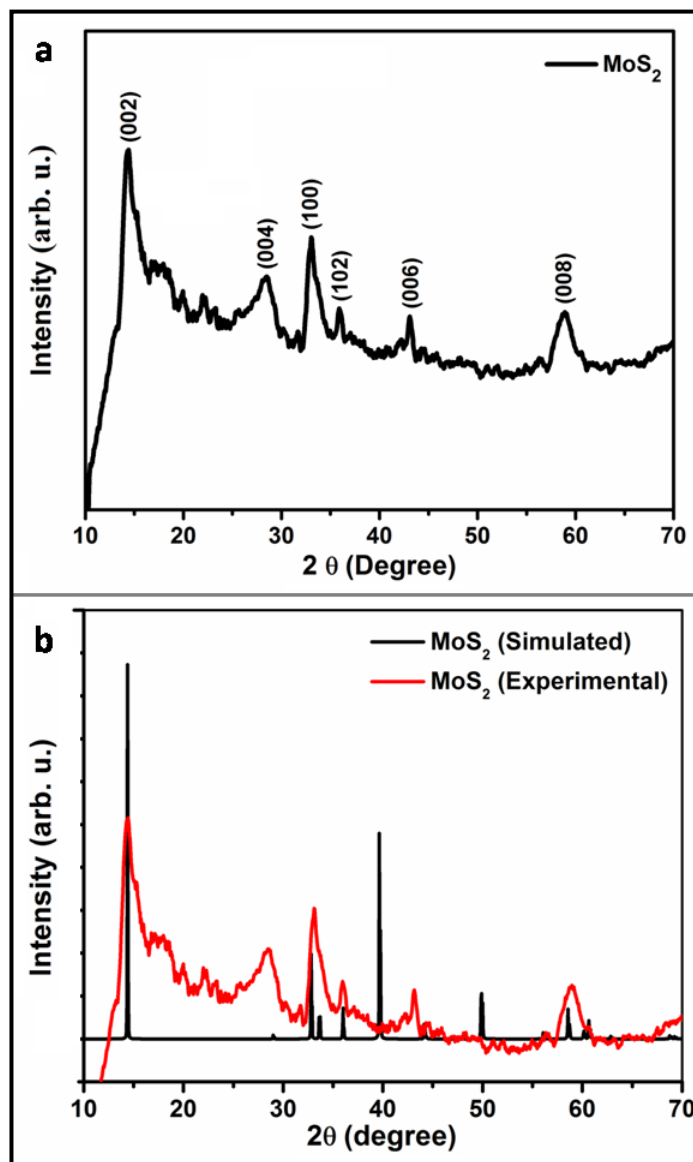


Figure 3.1 (a) XRD spectrum of MoS₂ NPs (experimental) and (b) Comparison of XRD of MoS₂ with simulated PXRD of MoS₂.

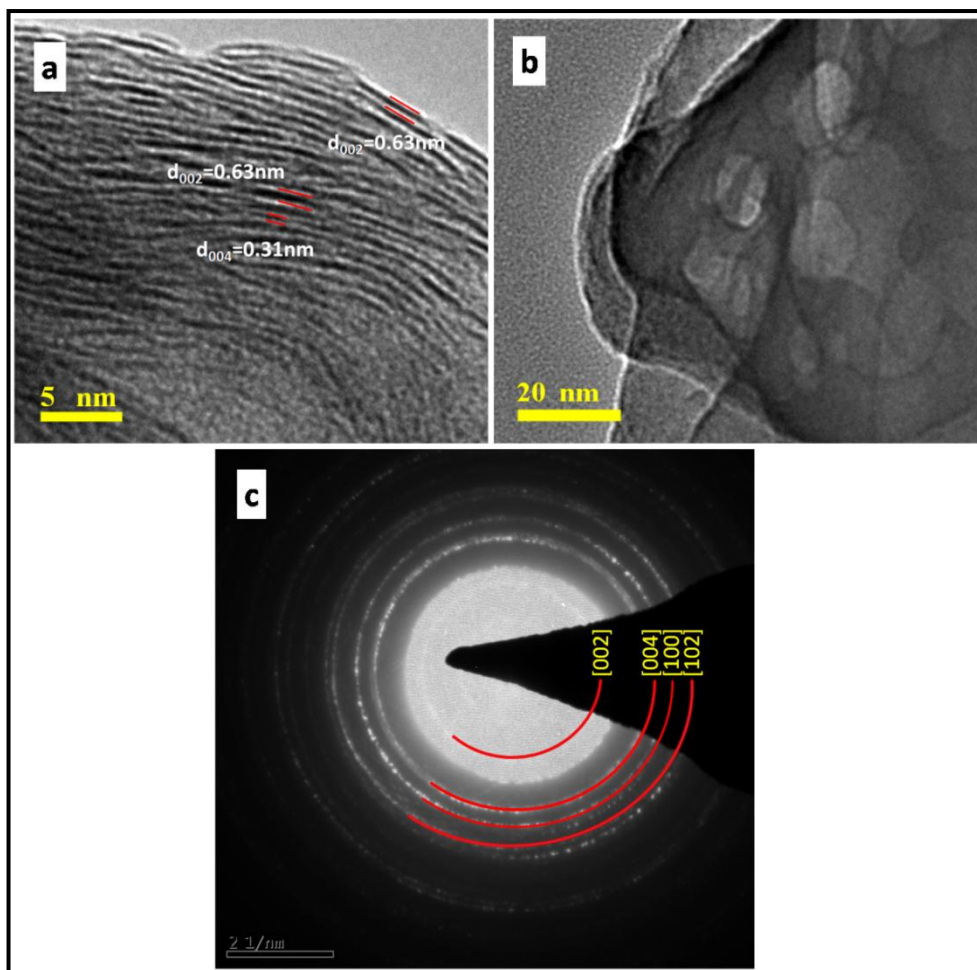


Figure 3.2 TEM image showing (a) different crystal planes, (b) a bunch of grains and (c) SAED pattern in MoS₂ NPs sample.

energy they got agglomerated and therefore, larger particles having nonuniform size distribution are also visible from the micrograph [3, 4].

In order to ascertain the composition of the material, we obtained the EDX spectrum of the MoS₂ NP sample. From the EDX spectrum analysis, given in figure 3.3(c), we conclude that the material is mainly composed of Mo and S, S being most abundant. The percentage composition of the MoS₂ NP sample is given in table 3.1. Both XRD spectra and EDX spectra revealed the formation of MoS₂. In the EDX spectrum, a characteristic peak near 2.31keV confirmed the presence of sulfur and near 2.39keV revealed the presence of Molybdenum in the respective sample [5]. Also, the abundance of specific elements and chemical composition of the as-synthesized MoS₂ NPs were envisioned in the elemental maps or spot chemical analysis using EDS given in figure 3.4.

Table 3.1 Percentage composition of MoS₂ from EDX spectrum.

Element	Weight %	Atomic %
S K	43.57	69.79
Mo L	56.43	30.21
Total	100.00	

Raman spectroscopy was also employed to study the vibrational mode of MoS₂ NP sample. We obtained Raman spectrum of the as-synthesized MoS₂ sample as it is the characteristic tool which provides a fingerprint by which the material can be identified. The Raman spectrum of the as-prepared sample was obtained with laser excitation wavelength of 488nm (2.54eV) as shown in figure 3.5.

The Raman spectrum here is given as a plot of the intensity of Raman scattered radiation as a function of its Raman shift (in units of wavenumber, cm⁻¹). The characteristic peaks 384.95cm⁻¹ and 406.12cm⁻¹ in the Raman spectrum of MoS₂ sample (figure 3.5(a)) revealed the Raman active vibration modes E_{2g}¹ and A_{1g} (figure 3.5(b)) in MoS₂ [6-8]. There is a shift in the position of E_{2g}¹ and A_{1g} mode from the bulk material at 383cm⁻¹ (E_{2g}¹) and 408cm⁻¹(A_{1g}) which is due to the low dimensional effect in the NPs. The blue-shift in E_{2g}¹ mode is due to the short-range coulombic interlayer interaction which changes the atomic vibration and the red-shift in A_{1g} mode is due to the smaller Van der Waals force which aids atomic vibration resulting in smaller force constant [7, 8]. Resonance

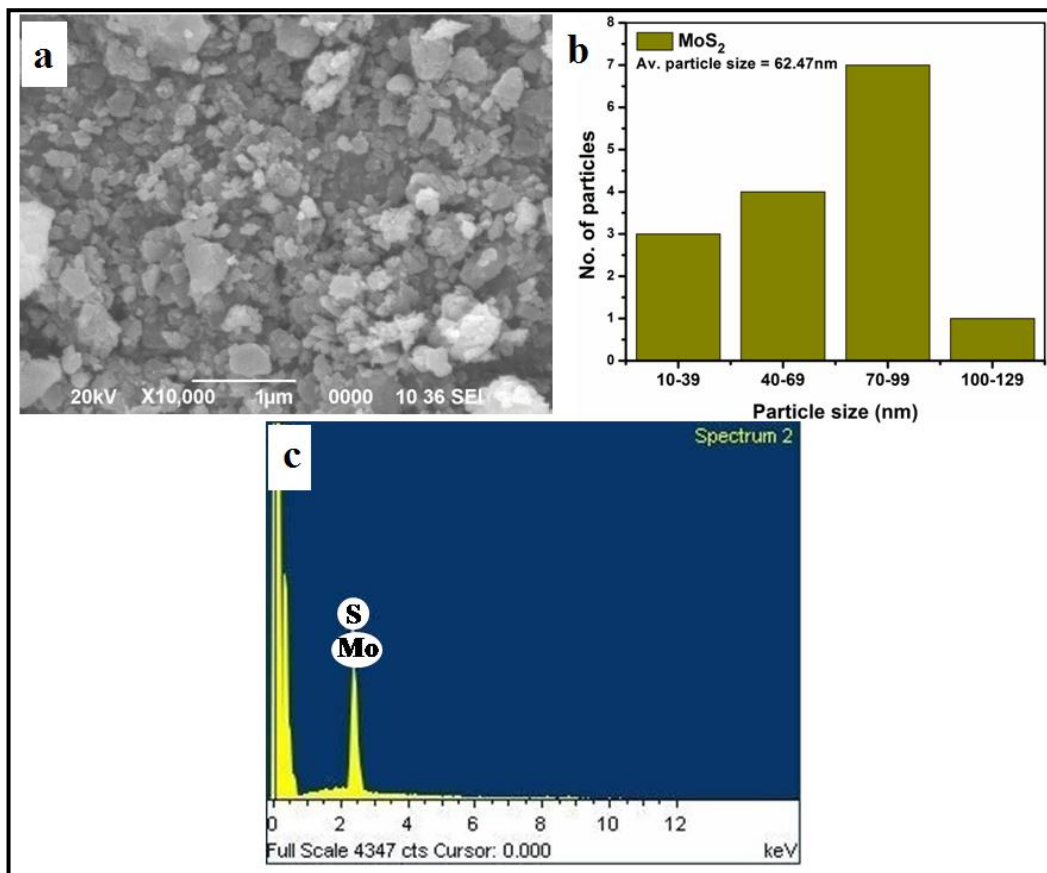


Figure 3.3 (a) SEM image, (b) particle size distribution histogram and (c) EDX spectrum of MoS₂ NPs sample. The noise peak observed below 0.5keV is not taken into consideration.

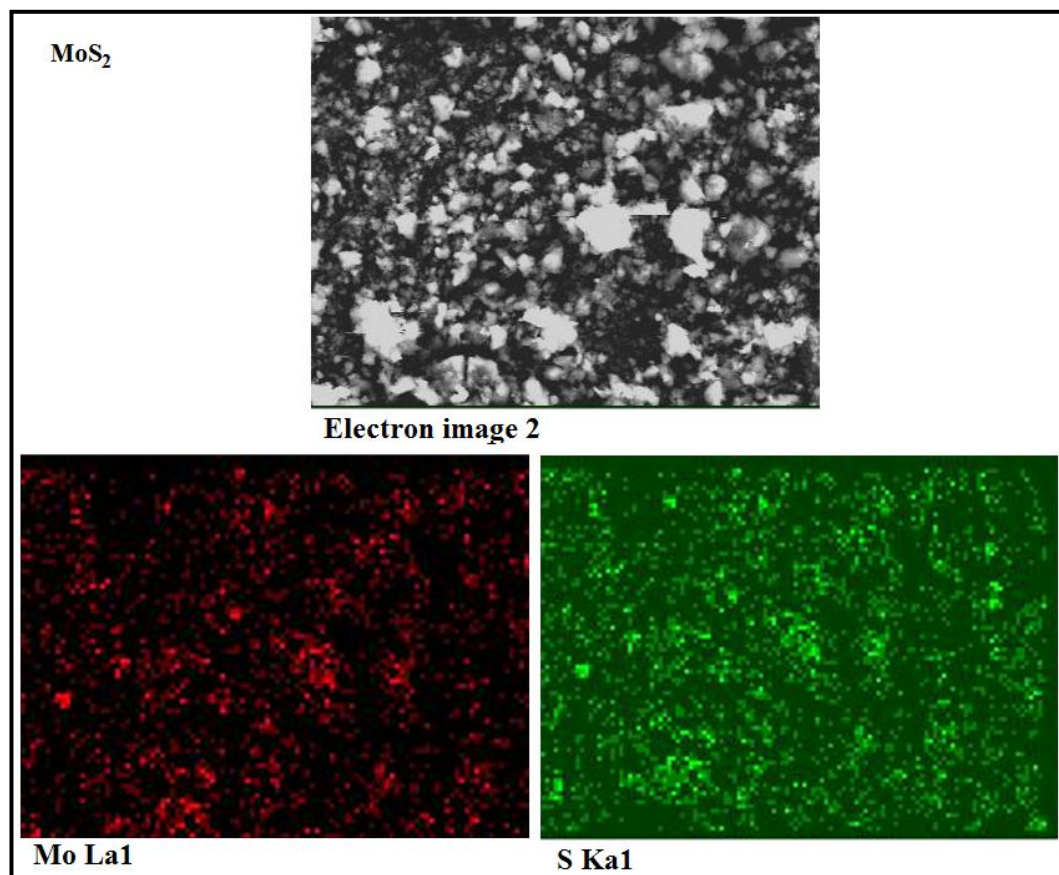


Figure 3.4 EDX spot Elemental mapping of MoS₂ NPs. The Bright spots represent the presence of respective elements in the image of Mo and S mapping.

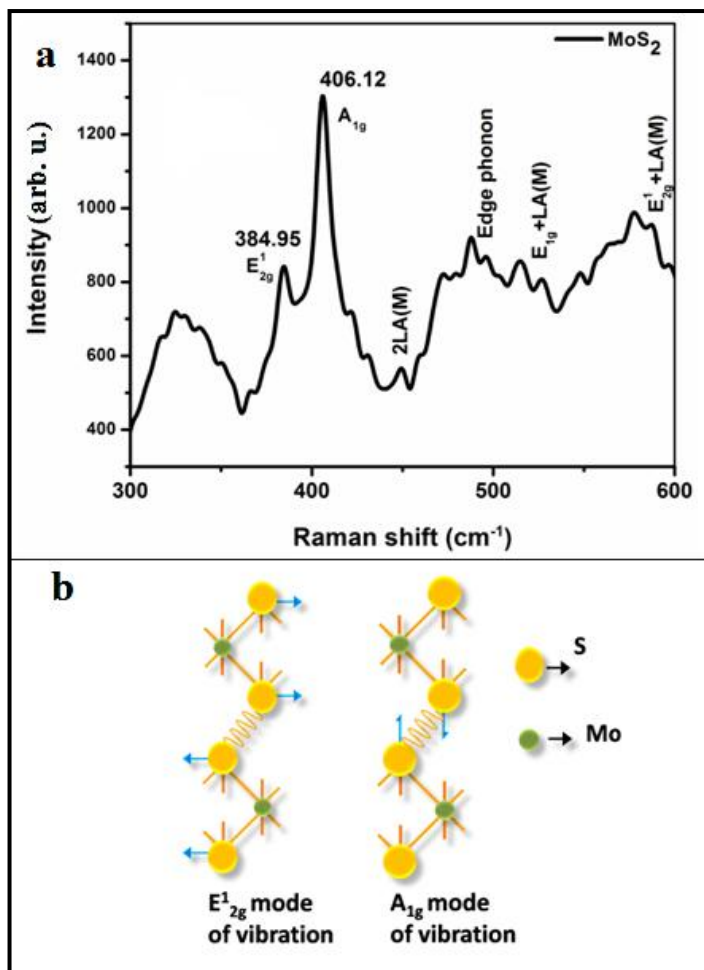


Figure 3.5 (a) Raman spectrum of MoS₂ NPs sample showing characteristics modes of vibration, (b) schematic to visualize prominent E_{2g}^1 and A_{1g} modes of vibration in MoS₂.

Raman peaks were also observed at 450cm⁻¹ (2LA(M)), 496 cm⁻¹ (Edge phonon), 526 cm⁻¹ (E_{1g} (M) + LA(M)) and 597cm⁻¹ (E_{2g}^1 (M)+LA(M)) because of the comparable value of excitation energy with the BG energy of the as-synthesized MoS₂ NPs [6].

Since Raman spectroscopy also detects phonon activity, the phonon lifetimes in the sample were also calculated using the energy-time uncertainty relation 3.2 [1]

$$1/\tau = \Delta E/h = \pi c \Gamma/2 \quad (3.2)$$

where ΔE is the uncertainty in energy, h is the Planck's constant, c is the speed of light in vacuum and Γ is the FWHM of the Raman peaks in cm⁻¹. The phonon lifetime corresponding to the Raman active modes E_{2g}^1 and A_{1g} obtained from Raman spectra for the as-synthesized MoS₂ NPs samples were found to be in the range of picoseconds (tabulated in table 3.2). The large phonon lifetime indicates that the samples have more defect states that may trap the phonon for a longer time [9].

Table 3.2 Determination of phonon lifetime in MoS₂ NPs sample from the Raman spectrum.

Peak position (cm ⁻¹)	Phonon Lifetime (ps)
384.95	3.39
406.15	2.78

Thus analyzing all the structural characterizations using XRD, SEM, TEM, EDX, Elemental mapping and Raman spectrum we conclude that the formation of MoS₂ NPs is confirmed. Also, it was observed that the average size of the NPs was 62.47nm having average crystallite size 11.07nm.

3.1.2 Optical characterizations of MoS₂ NPs

UV-vis spectrum and PL spectrum was analyzed and the optical BG value of the synthesized material was obtained using KM plot [10, 11]. The UV-Vis spectrum (inset in figure 3.6) reveals that there is good absorption of light in the visible region (500nm to 700nm) as well as in the UV region (250nm to 400 nm) for the as-synthesized MoS₂ NPs.

The presence of more than one edge in the spectrum also indicates different dimension or phases of the same material. For the MoS₂ NP sample, near 660nm and 610nm two absorption peaks are observed, which are due to ‘A’ and ‘B’ excitonic transitions as shown in figure 3.7 [12]. The lower energy peak is due to the transition from the upper level of the spin-split valence band (VB) to the conduction band (CB). Higher energy peak for the ‘B’ exciton is due to the transition from the lower spin-split level of VB to the CB near the k-valley position of Brillouin zone (BZ). Another absorption peak at around 400nm blue wavelength occurs due to the ‘C’ excitonic transition from VB to CB at band nesting position between Γ and Λ position of BZ [12-14]. In general electronic transitions may occur mainly in three different ways namely, (a) transition involving s, p and n electrons, (b) transition involving charge transfer and (c) transition involving d and f electrons. Both Mo (d block) and W (f block) are transition metals containing unfilled d orbitals. The transition in d-d or f-f orbitals corresponds to a UV-Vis range of light. The presence of S ligand in MoS₂ splits the d orbitals of Mo which in turn facilitate the electronic transition inside the crystal on exposure to radiation of suitable energy.

In order to determine the optical BG energy (E_g) of the as-synthesized material, we have applied the Kubelka Munk theory of diffused reflectance spectra [10]. The KM plot is similar to the Tauc Plot which is obtained from absorption spectra. The KM function $F(R)$ is obtained using relation (3.3).

$$F(R) = \frac{(1-R)^2}{2R} \quad (3.3)$$

where R is the reflection coefficient. The optical BG energy is determined using relation (3.4).

$$F(R)E = C_3(E - E_g)^{1/m} \quad (3.4)$$

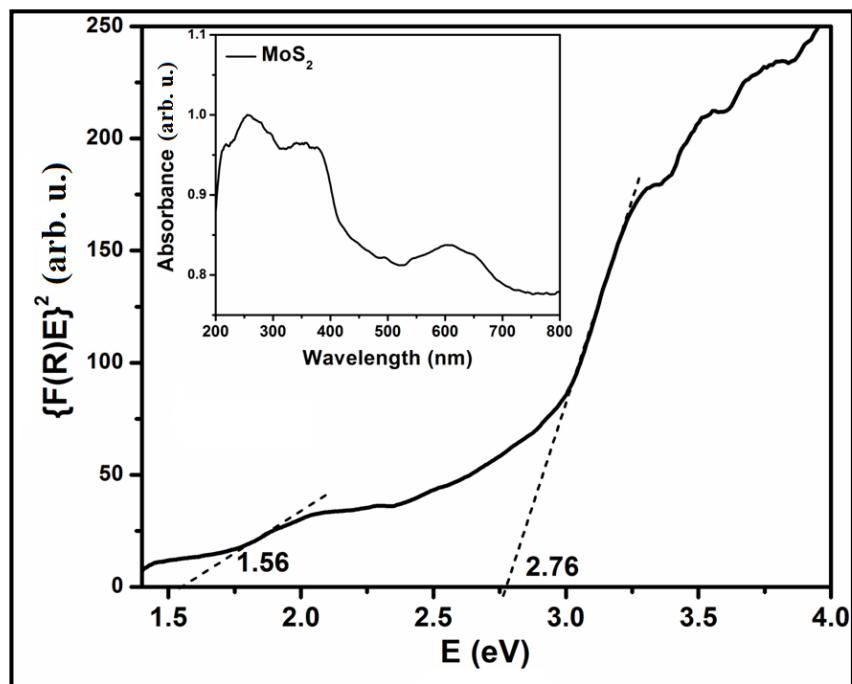


Figure 3.6 Optical BG determination by using KM plot of MoS₂ NPs (inset is UV-vis spectrum).

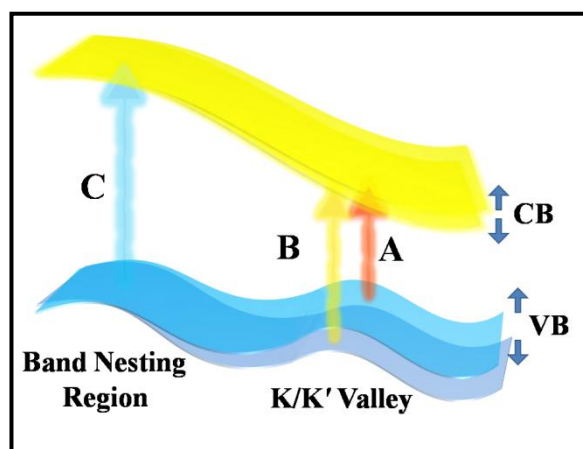


Figure 3.7 Schematic of 'A', 'B' and 'C' excitonic transition in TMDs.

where $m=2, 2/3, 1/2$ and $1/3$ are for direct allowed transition, direct forbidden transition, indirect allowed transition and indirect forbidden transition respectively, $E = hv$, the energy of radiation, h and v represents Planck's constant and frequency of vibration respectively. C_3 is the proportionality constant. The KM plot of the as-synthesized sample is shown in figure 3.6. The optical BG energy is determined by extrapolating the straight part of the KM plot as given in table 3.3.

Table 3.3 Optical energy BG calculation of MoS₂ NPs using KM plot.

Sample	E _g (eV)
MoS ₂	2.76, 1.56

It has been observed from KM plot that the transitions for the material is multiple and hence leads to multiple band gap (MBG) material. Large values of BGs is due to the 'C' excitonic transition at band nesting position [12, 14]. In MoS₂ there are two band gap values at 1.56eV and 2.76eV. The higher value of BG energy confirms the nano scale dimension of the material system [15].

The photoluminescence property of as-synthesized MoS₂ NPs is also studied. A comparative analysis of the luminescent nature of this sample along with other prepared samples is given in section 3.4 of this chapter.

3.2 Structural and optical properties of WS₂ NPs

3.2.1 Structural characterizations of WS₂ NPs

The structural characterizations of WS₂ NPs were also carried out in a similar way like that done for MoS₂ NPs. The powder XRD pattern of this sample is shown in figure 3.8(a). The simulated PXRD plot of WS₂ is also shown in comparison with the experimental XRD plot in figure 3.8(b). In the XRD pattern of WS₂ sample the peaks at 2θ values 14.36°, 32.77°, 33.59°, 35.94°, 39.60°, 44.29°, 49.79° and 58.49° correspond to (002), (100), (101), (102), (103), (104), (105) and (110) planes respectively (JCPDS No. 84-1398). The XRD also reveals hexagonal symmetry (SG:p6₃/mmc) in WS₂ lattice. The average crystallite size of WS₂ NPs calculated using relation 3.1 is obtained to be approximately 13.02 nm.

TEM micrograph is also obtained for the as-synthesized WS₂ NPs and is shown in figure 3.9(a). The crystal plane spacing of 0.62nm observed in the TEM micrograph shown in figure 3.9(a) corresponds to the Millar plane (002) in the WS₂ crystal. Figure 3.9(b) shows the SAED pattern of WS₂ NP sample as obtained using TEM. The SAED rings (100), (102) and (105) correspond to characteristic crystal planes of WS₂ NPs as obtained in the respective XRD pattern.

The SEM micrograph and EDX pattern of WS₂ NPs are shown in figure 3.10(a & c). The particle size distribution of WS₂ sample is measured from SEM micrographs. From the particle size distribution histogram in figure 3.10(b) it was found that the average particle size for WS₂ sample was 50.33nm. From the EDX spectra analysis, given in figure 3.10(c), we conclude that the composition of the sample is mainly W and S, S being most abundant (table 3.4). Both XRD spectra and EDX spectra reveal the formation of WS₂.

Table 3.4 Percentage composition of WS₂ from EDX spectrum.

Element	Weight%	Atomic%
S K	30.42	71.48
W L	69.58	28.52
Total	100.00	

In the EDX spectra characteristic peak near 2.31keV confirms the presence of sulfur and near 1.8keV, 7.29keV, 8.4keV, 9.8keV and 11.25keV represents tungsten in the respective sample [5, 16]. Analyzing the elemental mapping using EDX spectroscopy the abundance of specific elements and chemical composition of the as-synthesized WS₂ NPs

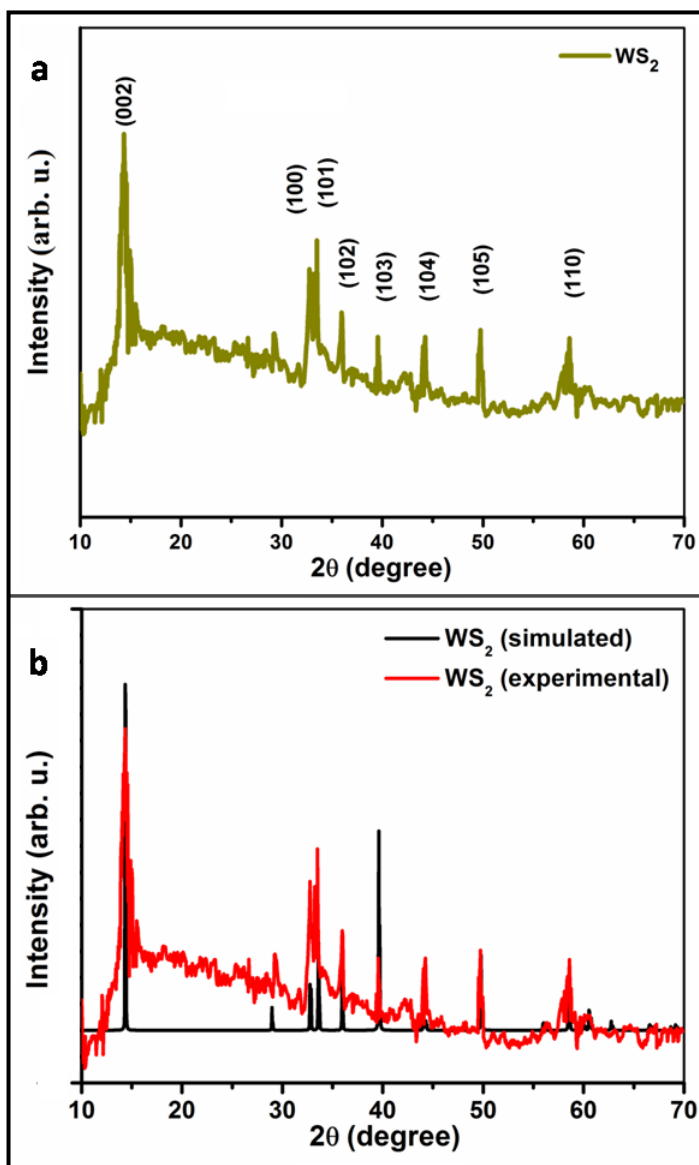


Figure 3.8 (a) XRD pattern of WS₂ NPs showing different characteristic peaks corresponding to Miller crystal planes and (b) Comparison of XRD pattern of WS₂ with simulated PXRD of WS₂.

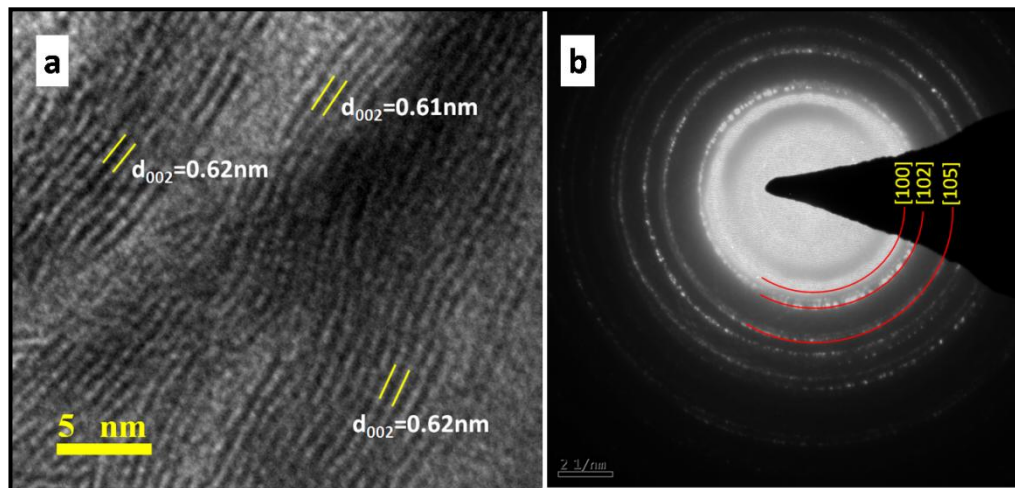


Figure 3.9 (a) TEM micrograph and (b) SAED pattern of WS₂ NPs sample.

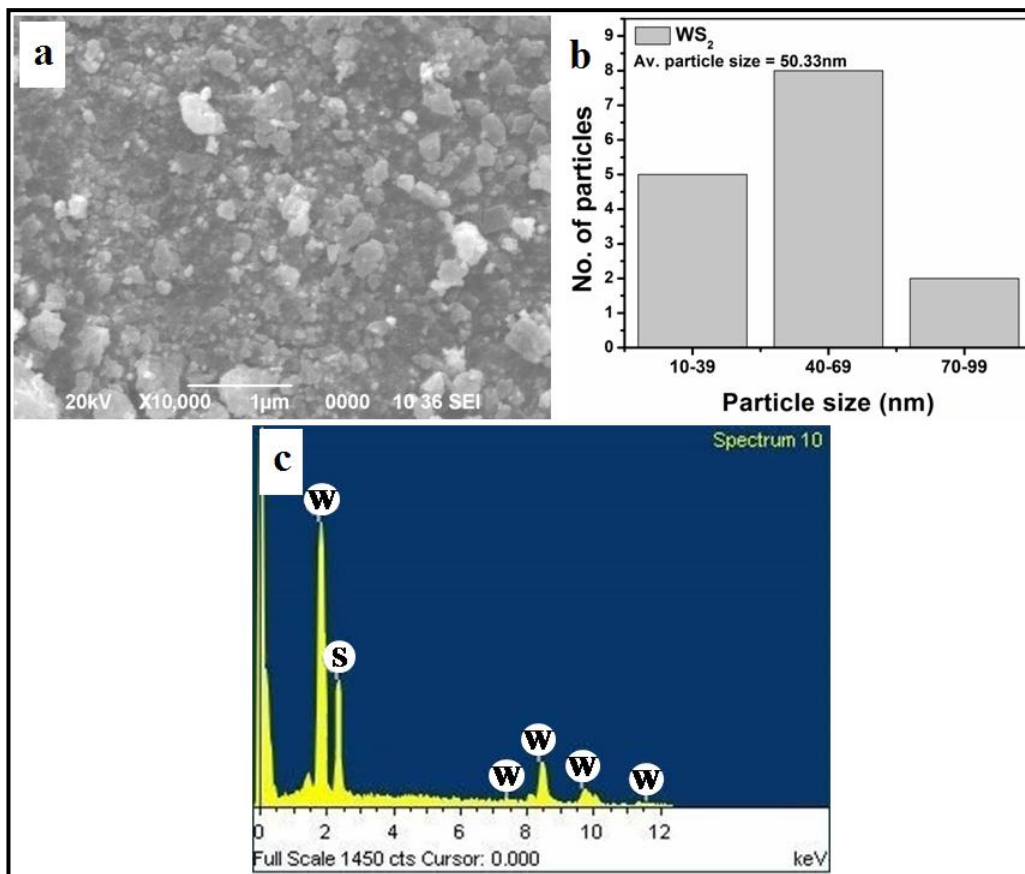


Figure 3.10 (a) SEM image, (b) particle size distribution and (c) EDX spectrum of WS₂ NPs sample. The noise peak observed below 0.5keV is not taken into consideration.

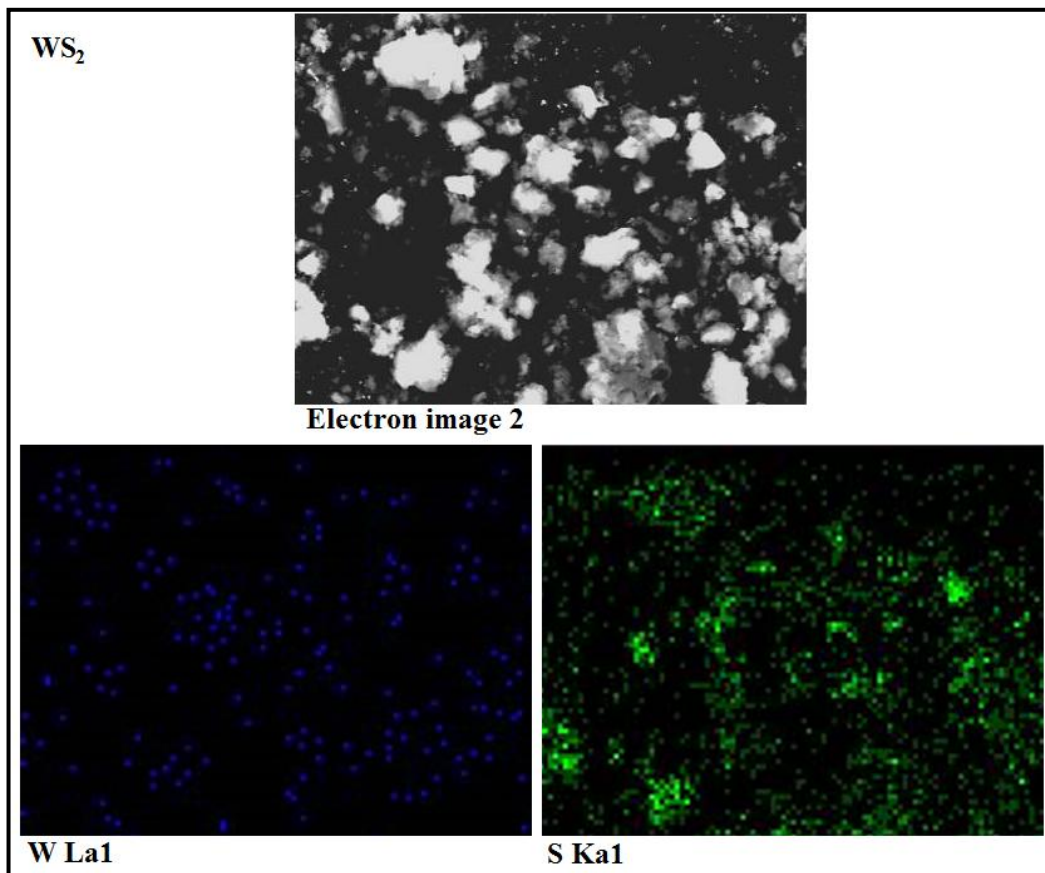


Figure 3.11 EDX elemental mapping of WS₂ NPs sample. The bright spots in a black background in the second and third image represent the positions of respective elements W and S in the selected area.

are clearly visualized as given in figure 3.11.

In figure 3.12 the Raman spectrum of WS₂ NPs is shown. The characteristic peaks 348.34cm⁻¹ and 420.01cm⁻¹ in the Raman spectrum of WS₂ NPs sample reveal the Raman active vibrational mode E_{2g}¹ and A_{1g} in WS₂. There is also shift in the two prominent modes in the WS₂ NPs sample from that of bulk structure, which may be due to the similar effect like that for MoS₂ sample as described in section 3.1.1[7, 8]. The resonance mode A_{1g} + LA(M) at 593.07cm⁻¹ which may occur due to comparable excitation energy with BG value of the material is also recognizable. The phonon lifetime is calculated from the Raman active mode peaks and is tabulated in table 3.5. Here also the phonon lifetimes corresponding to the prominent Raman active modes E_{2g}¹ and A_{1g} are found to be in picosecond range like that of MoS₂ NP sample indicating defective traps in the NPs.

Table 3.5 Determination of phonon lifetime in WS₂ NPs sample from Raman spectrum.

Peak position (cm ⁻¹)	Phonon Lifetime (ps)
348.34	1.67
420.01	1.96

3.2.2 Optical characterizations of WS₂ NPs

The UV-Vis spectrum of the WS₂ NP sample is shown in the inset of figure 3.13. The spectrum shows good absorption of light in the visible region as well as in the UV region. The KM plot of the WS₂ NPs sample is shown in figure 3.13. The optical BG (E_g) energy is determined from the KM plot and tabulated in table 3.6. Like MoS₂ NPs sample, we have also observed two BG values which are probably due to a different phase or dimensional effect [17, 18].

Table 3.6 Optical Energy BG calculation of WS₂ NPs using KM plot.

Sample	E _g (eV)
WS ₂	2.74, 1.58

The PL property of the as-synthesized WS₂ NP is also studied. A comparative analysis of the luminescence property of this sample along with other prepared samples is given in section 3.4 of this chapter.

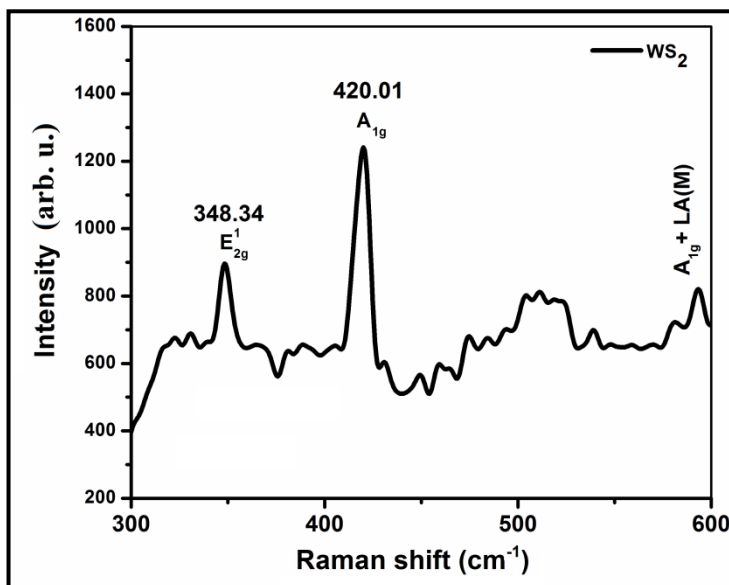


Figure 3.12 Raman spectrum of WS₂ NPs showing prominent Raman active modes in the sample.

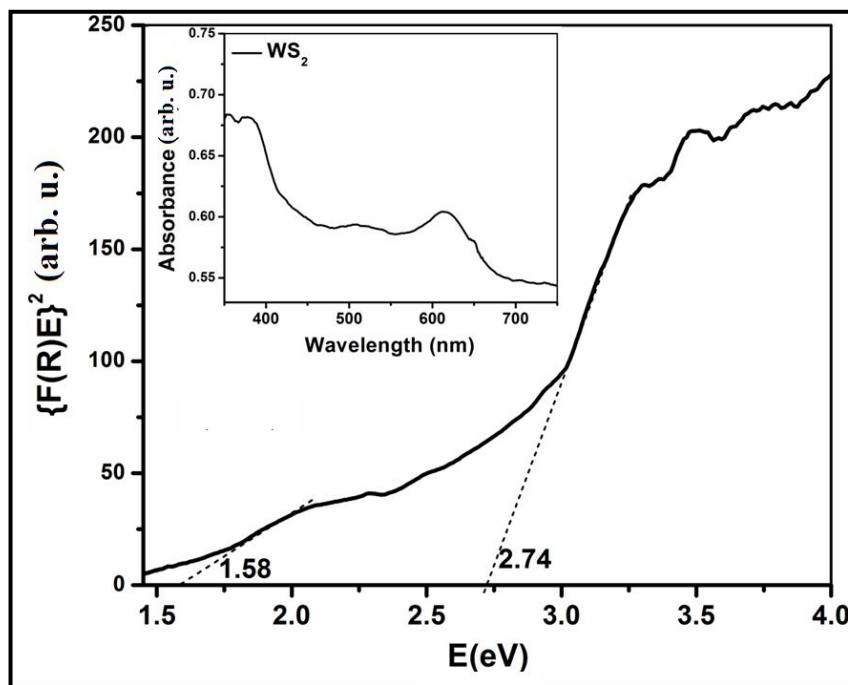


Figure 3.13 Optical BG determination by using KM plot of WS₂ NPs (inset is UV-vis spectrum).

3.3 Structural and optical properties of ternary MoW-disulfide compound NPs

3.3.1 Structural characterizations of ternary MoW-disulfide compound NPs

The plots of figure 3.14 show the XRD patterns for the four prepared sample materials namely MoS₂, WS₂, MoW-disulfide1 and MoW-disulfide2 NPs. The different crystal planes in the XRD plot (iii) and plot (iv) in figure 3.14 revealed the crystallinity of the as-prepared compound materials. In plot (i) and plot (ii) of figure 3.14, the prominent characteristic peaks and various crystal planes of MoS₂ and WS₂ NPs are revealed. The XRD patterns as shown by the plot (iii) and plot (iv) of the MoW-disulfide1 and MoW-disulfide2 samples are quite different from that of MoS₂ and WS₂ NPs. This outcome indicated the possible formation of new bonding structures between Mo, W and S. This result provides us information about the formation of a ternary disulfide compound of Mo and W. In comparison with MoS₂ and WS₂ structures, the different possible crystal plane positions were obtained in the respective XRD plots of the compounds. The possible Miller planes corresponding to respective 2θ values and d-spacing values for ternary compounds are tabulated in table 3.7 and table 3.8. The d spacing values are obtained using Bragg's law of diffraction in crystal planes and are given by formula 3.5.

$$d_{hkl} = \frac{m\lambda}{2\sin\theta} \quad (3.5)$$

where d_{hkl} is the spacing between consecutive crystal planes, λ and θ are the wavelength of X-ray used and Bragg's angle respectively, m is the order of diffraction which is equal to one in our current study.

Table 3.7 2θ, Millar planes and d-spacing values for MoW-disulfide1 NPs.

2θ (degree)	23.12	28.75	33.17	34.17	35.49	44.57	49.76	59.84
d-spacing (Å)	3.85	3.10	2.69	2.62	2.53	2.03	1.83	1.54
Miller Plane	(003)	(004)	(100)	(101)	(102)	(006)	(105)	(008)

The average crystallite sizes (L) of MoW-disulfide1 and MoW-disulfide2 are calculated using the Debye-Scherrer formula 3.1 and found to be 22.02nm and 18.30nm respectively. The increase in crystallite size in the as-synthesized compound

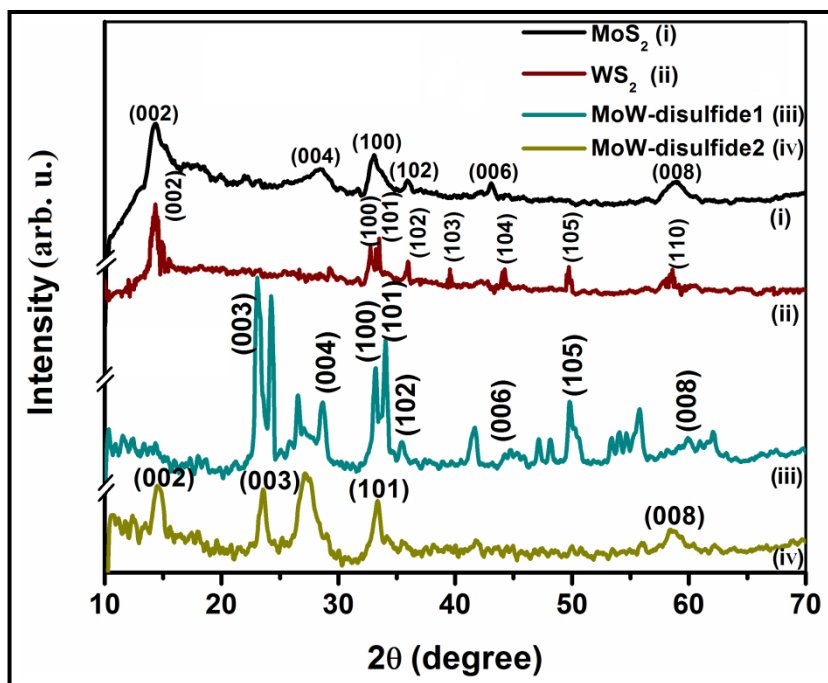


Figure 3.14 XRD patterns of (i) MoS₂, (ii) WS₂, (iii) MoW-disulfide1 and (iv) MoW-disulfide2 NPs sample.

Table 3.8 2 θ , Miller planes and d-spacing values for MoW-disulfide2 NPs.

2θ (degree)	14.52	23.53	33.41	59.01
d-spacing (Å)	6.10	3.78	2.68	1.56
Miller Plane	(002)	(003)	(101)	(008)

MoW-disulfide1 relative to MoS₂ and WS₂ reflects that W forms a better crystal with S compared to Mo. In MoW-disulfide2 the crystallite size again decreases as the concentration of W compared to Mo decreases. Therefore, it reaffirms the fact that the combination of W and S leads to better crystallinity than the combination of Mo and S.

The TEM micrographs of the compound MoW-disulfide1 and MoW-disulfide2 NPs are also analyzed to study the crystal planes present in the as-prepared samples. Figure 3.15 shows the TEM images where different possible Miller planes are indicated in the compound NPs. TEM analysis confirms that the NPs are polycrystalline in nature. The interplanar spacings 0.31nm and 0.39nm measured from in the TEM micrograph 3.15(a) are possibly be due to (004) and (003) Miller planes respectively in MoW-disulfide1 NPs and spacings 0.63nm and 0.40nm in figure 3.15(b) represent Miller planes (002) and (003) respectively in MoW-disulfide2 NPs considering the structure of the ternary compound to be hexagonal, the most stable structure in case of TMDs. The results of XRD and TEM, both reveal that the possible crystal structure of the compound NP is hexagonal like that of MoS₂ and WS₂.

The SEM micrographs along with the particle size distribution of the as-synthesized ternary compound materials are shown in figure 3.16. The average particle sizes for MoW-disulfide1 and MoW-disulfide2 NPs are found to be 51.40nm and 57.26nm respectively (figure 3.16(b & e)). The agglomeration of particles is also visible in the SEM micrographs.

From the EDX spectra, given in figure 3.16(c & f), we conclude that MoW-disulfide1 and MoW-disulfide2 are mainly composed of Mo, W and S, S being most abundant. The abundance of W in MoW-disulfide1 is richer than that of MoW-disulfide2. Both XRD spectra and EDX spectra reveal the formation of ternary MoW-disulfides compound.

In the EDX spectra in figure 3.16(c & f) characteristic peaks at 2.31keV confirm the presence of sulfur; at 2.39keV reveal the presence of molybdenum and near 1.8keV, 7.29keV, 8.4keV, 9.8keV and 11.25keV represent the presence of tungsten in the

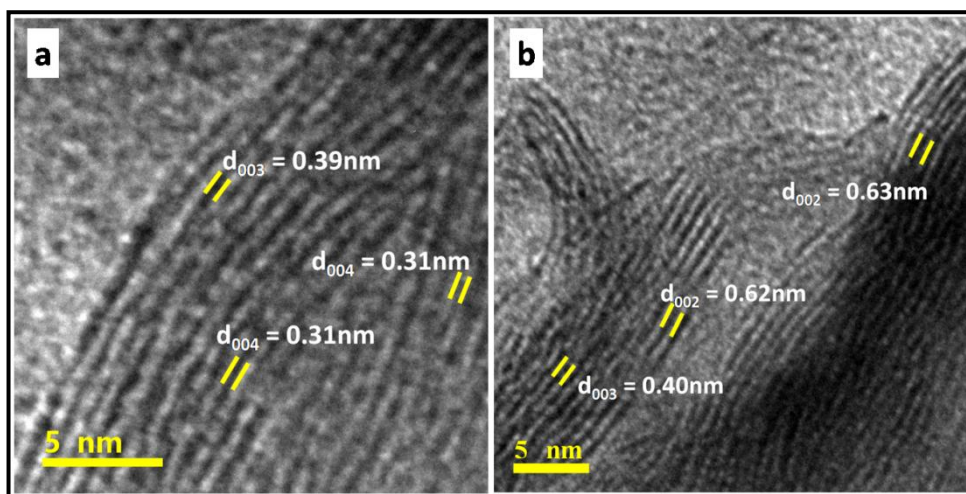


Figure 3.15 TEM micrograph of (a) MoW-disulfide1 and (b) MoW-disulfide2 showing different Miller planes.

respective samples. From the EDX spectrographs of the compound materials, the weight% and atomic% along with the characteristic transition levels are tabulated in table 3.9 and table 3.10. From table 3.9 and table 3.10, it is found that in MoW-disulfide1 the main

Table 3.9 Percentage composition of MoW-disulfide1 from EDX spectrum.

Element	Weight%	Atomic%
S K	23.25	60.36
Mo L	11.79	10.23
W M	64.96	29.41
Total	100.00	

Table 3.10 Percentage composition of MoW-disulfide2 from EDX spectrum.

Element	Weight%	Atomic%
S K	63.34	86.23
Mo L	23.31	10.60
W M	13.35	3.17
Total	100.00	

elements present are Mo, W and S with Mo:W atomic % ratio 1:3, and in MoW-disulfide2 Mo:W atomic % ratio 3:1, S being most abundant in both MoW-disulfide1 and MoW-disulfide2. Also, the presence of the characteristic peaks of Mo, W and S in EDX spectra confirms their existence in the respective materials. The abundance of specific elements and chemical composition of the as-synthesized ternary compounds are envisioned in the elemental maps or spot chemical analysis using EDX spectroscopy given in figure 3.17 and figure 3.18. The bright spots in the mapped images represent the corresponding element which could be visualized due to the characteristic transition Ka₁ for S, La₁ for Mo and La₁ for W atoms [5, 16].

Raman spectra of the compounds MoW-disulfide1 and MoW-disulfide2 were also obtained and are shown in figure 3.19. The Raman spectra of these materials were obtained at laser excitation wavelength of 488nm (2.54eV) as obtained in the case of MoS₂ and WS₂ NPs. The characteristic peaks obtained in case of MoS₂ are also observed in the Raman spectrum (figure 3.19(b)) of MoW-disulfide2 having smaller W content with slight shift in peaks which is due to the dominant effect of larger Mo content; but in case of MoW-disulfide1 having larger W content, no significant results could be drawn in the absence of recognizable peaks (figure 3.19(a)). However the formation of new bonds cannot be ruled

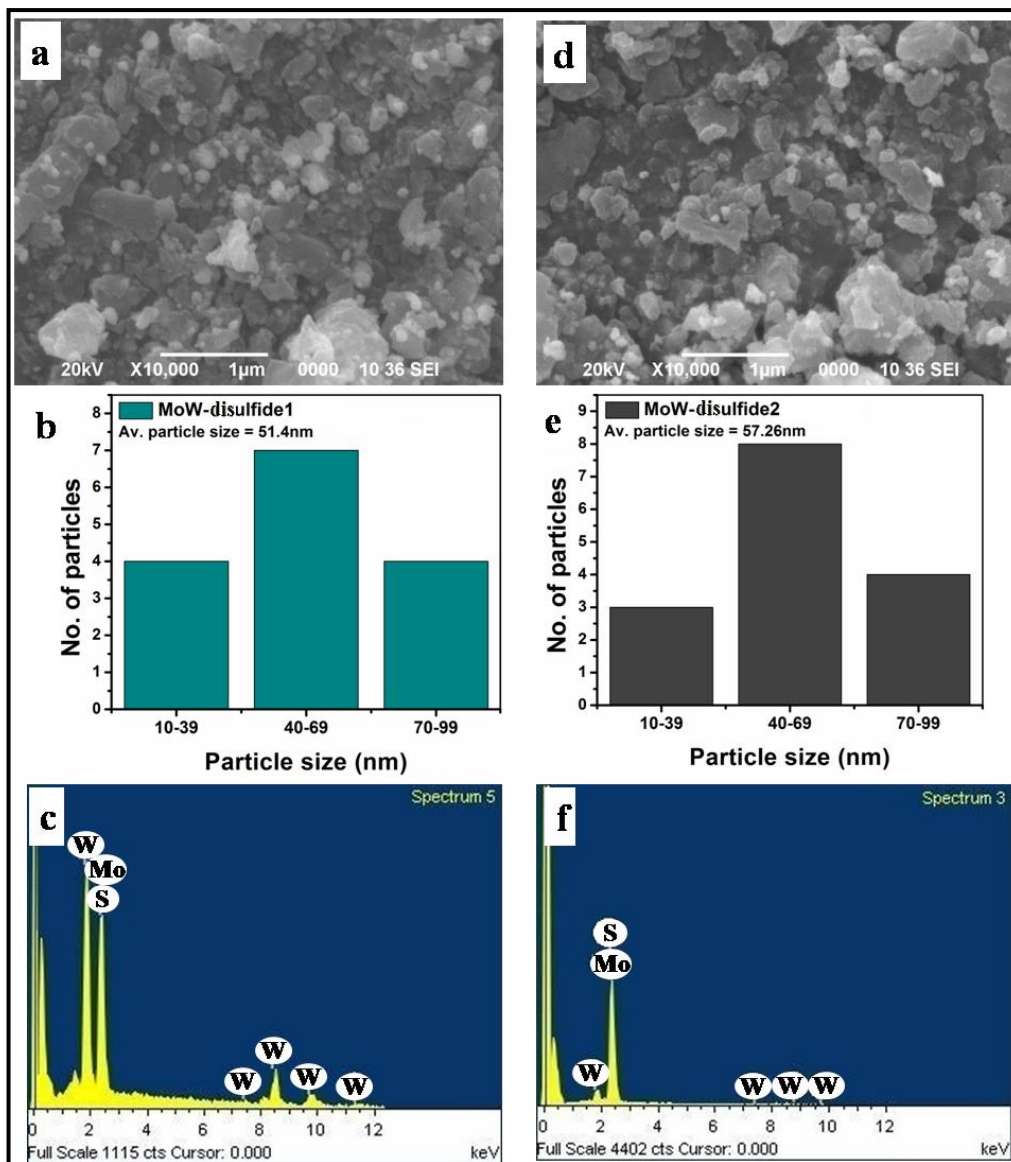


Figure 3.16 Figure shows (a) SEM image, (b) particle size distribution and (c) EDX spectrum of MoW-disulfide1 NPs and (d) SEM image, (e) particle size distribution and (f) EDX spectrum of MoW-disulfide2 NPs.

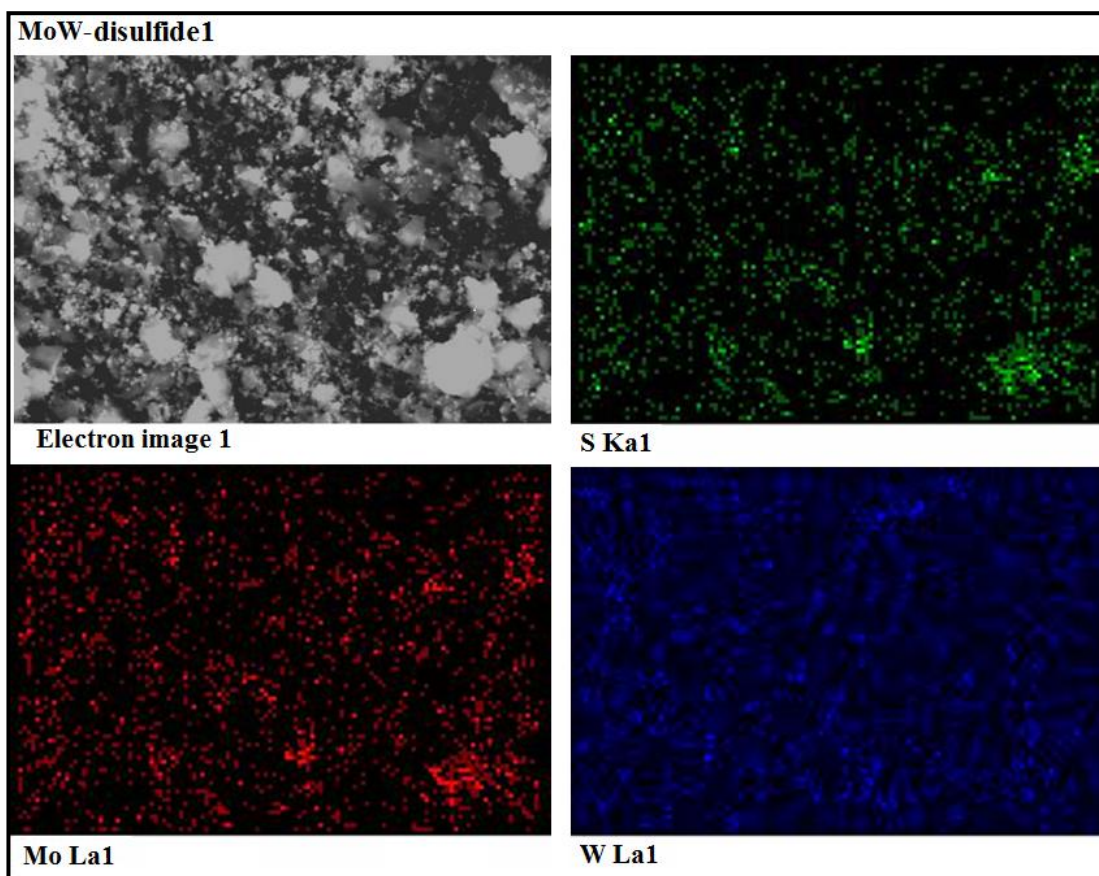


Figure 3.17 EDX Elemental mapping of MoW-disulfide1. The bright spots in black background in the second, third and fourth images represent the positions of respective elements S, Mo and W in the selected area.

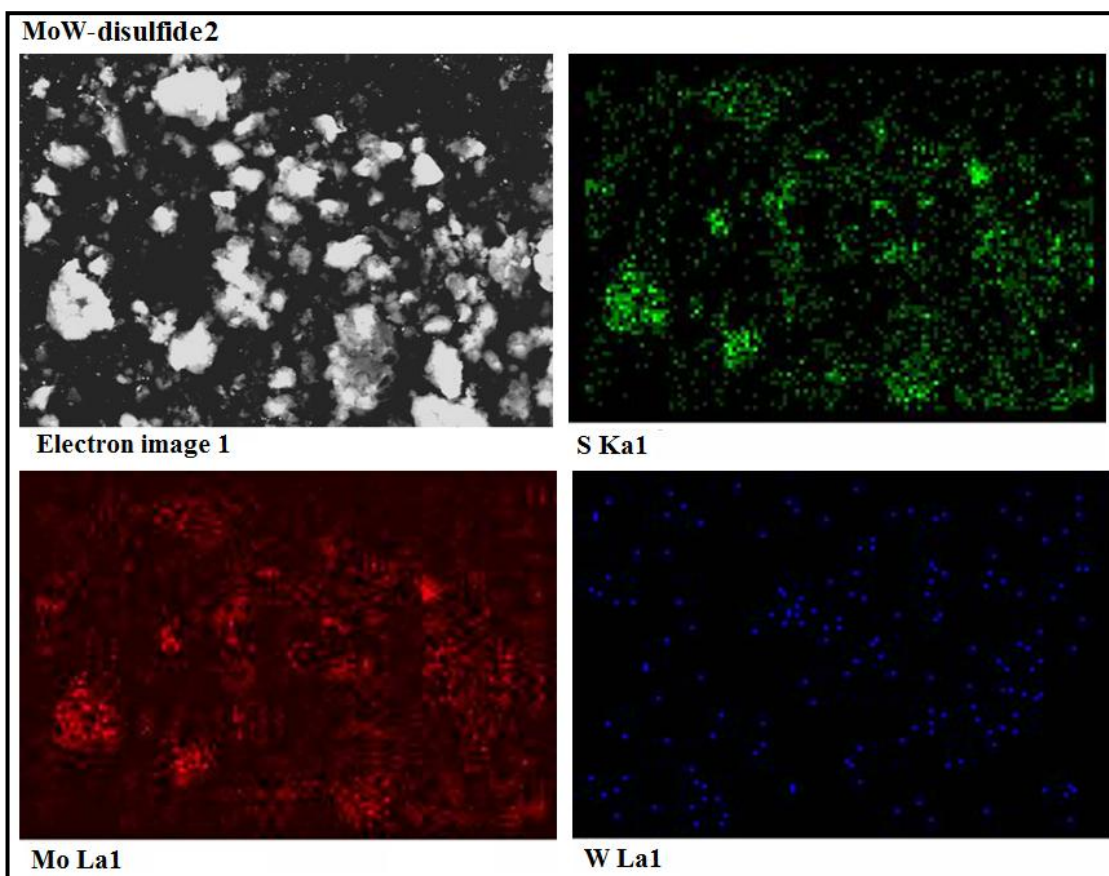


Figure 3.18 EDX Elemental mapping of MoW-disulfide2. The bright spots in black background in the second, third and fourth images represent the positions of respective elements S, Mo and W in the selected area.

out. The phonon lifetimes of the ternary dichalcogenide NPs corresponding to prominent Raman peaks are calculated using the energy-time uncertainty relation 3.2 and are tabulated in table 3.11. Large values of phonon lifetime in the picosecond range depict the stability of phonons in the defects of the ternary compound NPs.

Table 3.11 Determination of phonon lifetime in MoW-disulfide1 and MoW-disulfide2 samples from the Raman spectra.

Sample	Peaks(cm^{-1})	Phonon lifetime (ps)
MoW-disulfide1	329.96	2.39
MoW-disulfide2	382.08	2.49
	404.57	2.34

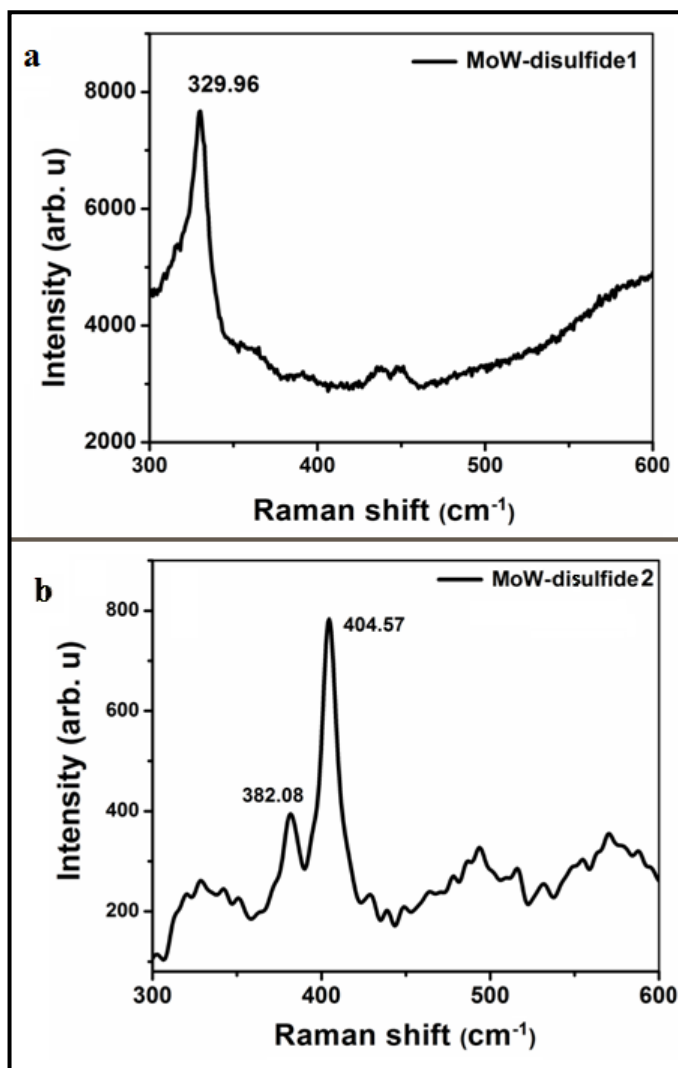


Figure 3.19 Raman spectra of (a) MoW-disulfide1 NPs and (b) MoW-disulfide2 NPs.

3.3.2 Optical characterizations of ternary MoW-disulfide compound NPs

In figure 3.20 we show the KM plots obtained from UV-vis spectra of the two as-synthesized compound materials namely MoW-disulfide1 and MoW-disulfide2 NPs. The inset of figure 3.20 shows the UV-vis spectra of the two compounds. The nature of absorption of light of these prepared compound NPs is not different from that of MoS₂ and WS₂ NPs. The absorption spectra reveal good absorption of light in both UV and visible wavelengths by the two compounds. From the KM plot, the optical BG energy values are determined for the two compounds and given in the table 3.12. KM plot indicates the existence of multiple transitions in the NP materials and hence allows MBG values. Due to transition at band nesting position there exist high values of optical BGs in the compound materials [12-14]. In MoW-disulfide2, there are two band gap values whereas in MoW-disulfide1 there are possibly three BG values. The dominance of W in MoW-disulfide1 may be the reason behind having an extra band gap value compared to the other compound sample.

Table 3.12 Optical Energy BG calculation of MoW-disulfide1 and MoW-disulfide2 using KM plot.

Sample	E _g (eV)
MoW-disulfide1	2.84, 2.41, 1.65
MoW-disulfide2	2.65, 1.45

From table 3.12 it is found that the compound ternary disulfide1 have the highest BG energy which corresponds to visible blue light wavelength. The increase in BG for this sample is due to the insertion of a bigger atom like W in the lattice site of MoS₂. Actually, the above anomalies in MoW-disulfide1 may be due to the combined effect of ligand S and W which leads to spin splitted d-orbitals that raise the energy levels and provides an extra energy gap value as well. This, in turn, increases the BGs. As the size of the material reduces, the number of overlapping orbitals or energy levels (both bonding and antibonding orbitals) decreases. This results in narrower bands and the band gap increases. The high BG energy of the ternary compound samples confirms the nanoscale dimension of the material system [15].

The PL behavior of the as-synthesized ternary compound NPs is given in the following section 3.4 and compared with MoS₂ and WS₂ NP samples.

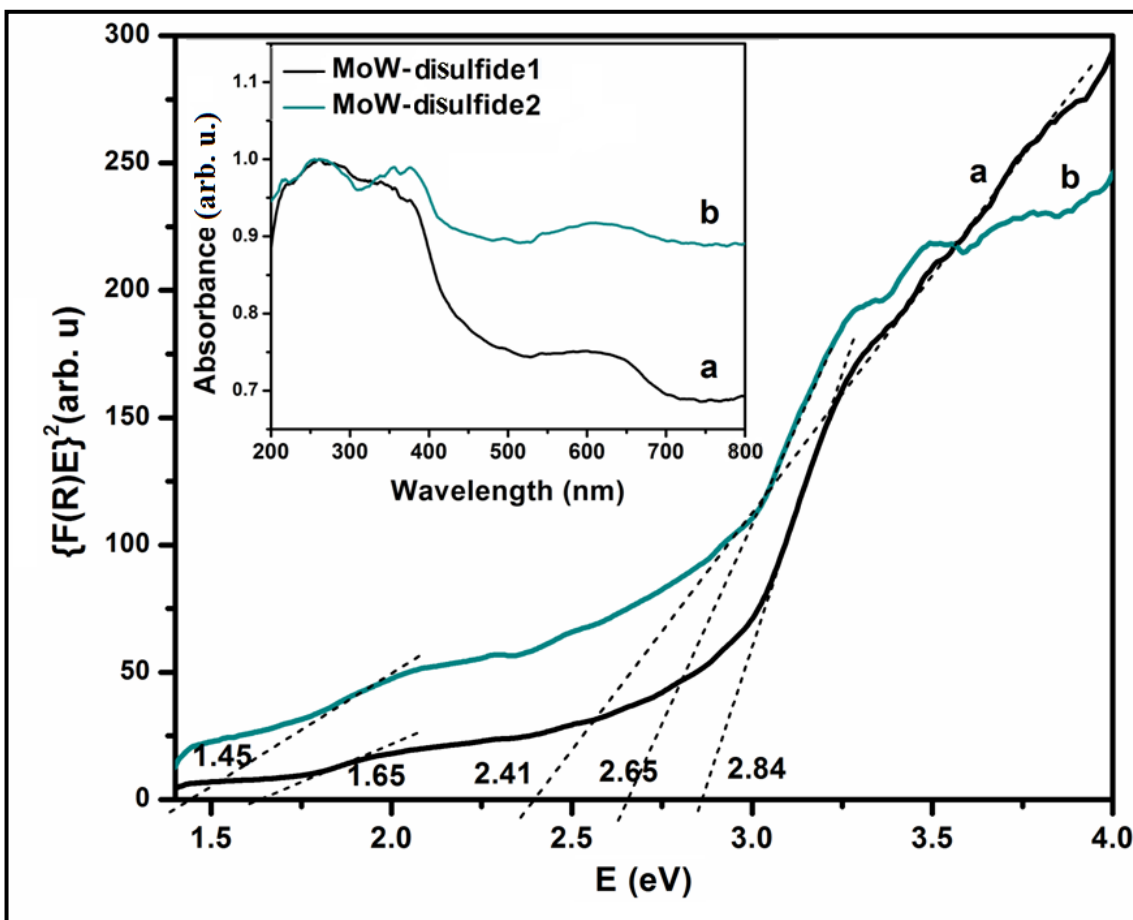


Figure 3.20 Optical BG determination by using KM plot of compound (a) MoW-disulfide1 and (b) MoW-disulfide2 NPs (inset is UV-vis spectra).

3.4 Study of photoluminescence spectra of MoS₂, WS₂, MoW-disulfide1, and MoW-disulfide2 NPs

Being SCs, PL is investigated in our as-synthesized materials. The PL spectra of the as-synthesized materials are shown in figure 3.21. We have analyzed the PL spectra to measure the emission BG of new compound SC NPs as well as MoS₂ and WS₂ NPs. The chosen excitation wavelengths are in the UV (300nm) region in plot 3.21(a) and Visible (500nm) region in plot 3.21(b).

Analyzing the PL spectra in figure 3.21, it has been observed that there is an enhancement in the luminescence of the compound disulfide having larger W:Mo ratio. The luminescence peaks are observed at approx. 659nm (1.88eV) for excitation wavelength of 500nm and at approx. 462nm (2.68eV) for excitation wavelength of 300nm. In case of MoW-disulfide1 NPs, the PL peak is enhanced by about two times compared to that of MoS₂ NPs and 1.7 times than that of WS₂ NPs. It is observed that WS₂ NPs have slightly higher PL intensity than that of MoS₂ NPs. This may be due to the effect of a larger W atom which provides more exciton pairs compared to MoS₂ NPs. The compound disulfides of W and Mo combination having larger W content give rise to an increase in luminescence. Larger W content in the ternary compound enhances the PL intensity. This is probably due to the increase in the number of photo-excitons with the insertion of W in a large amount and as a consequence higher density of generated photo-excitons increases the PL intensity by the process of radiative recombination. It can also be due to the presence of less number of defects in compound disulfide1 as it has the highest value of crystallite size [20]. The near BG emission in the PL spectra also reveals the possibility of direct BG nature of the as-synthesized dichalcogenides and the PL can be considered to be band edge emission. We have also investigated the effect of W and Mo in their ternary compound theoretically using DFT based software. DFT investigation (discussed in chapter 5) reveals that W insertion in the MoS₂ system leads the system towards becoming direct BG SC which, in turn, may lead to enhanced PL emission as observed in our experiment. In figure 3.22 a schematic of photoexcitation and radiative recombination of exciton pairs is described.

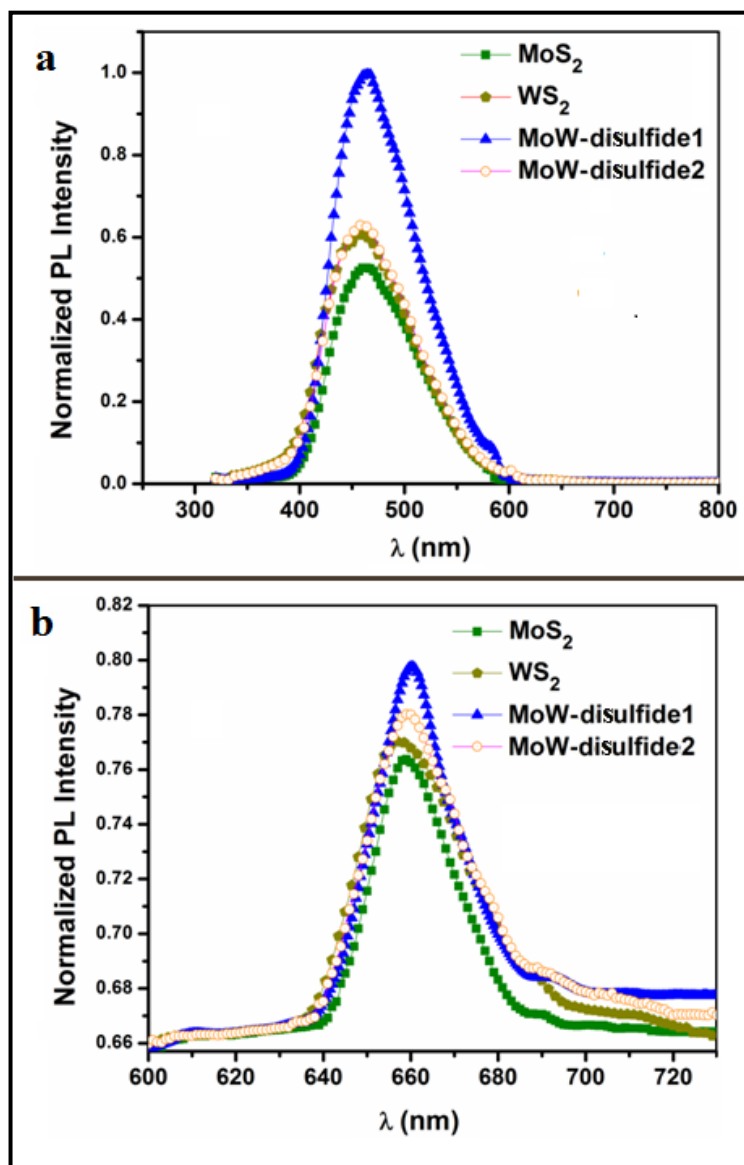


Figure 3.21 PL spectra of MoS₂, WS₂, MoW-disulfide1 and MoW-disulfide2 at (a) 300nm (4.13eV) and (b) 500nm (2.48eV). The enhancement of PL peak is observed in case of ternary compound MoW-disulfide1 having largest normalized intensity.

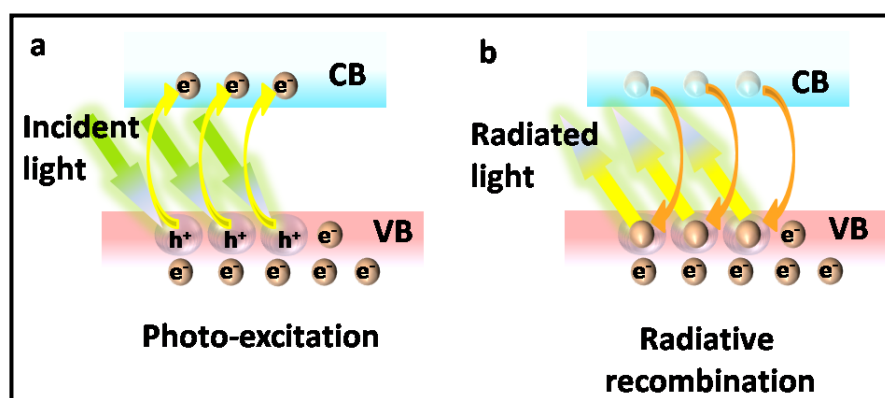


Figure 3.22 The figure shows (a) the excitation of a direct BG semiconductor by light radiation generating electron-hole pairs and (b) re-emission of light by the process of radiative recombination of electron and holes.

3.5 Conclusions

In this chapter we have reported the structural properties, optical emission properties and chemical composition of the as-synthesized SC TMDs compound NPs along with MoS₂ and WS₂ NPs. XRD, SEM, TEM, EDX and Raman spectra analyses reveal the formation of desired materials having nanoscale size distributions. It has been observed from UV-Vis and PL spectra that the combining effect of the sulfides of W and Mo gives rise to different optical properties. Enhanced blue PL emission near 463nm in MoW-disulfide¹, having Mo:W molar ratio equal to one, indicates the material's good applicability in luminescence devices. Also, multiple band gaps of the ternary compound promise the material to be a good material for photocatalytic activity.

[Note: This work is published in the Journal Bulletin of Materials Science.

Kalita, D., Chetia, L. Chetri, P., and Ahmed, G. A. Investigation of structural and luminescence properties of nanocrystalline Tungsten incorporated Molybdenum disulfide ternary compounds: An Experimental and DFT Study. *Bull. Mater. Sci.*, 42:134, 2019. DOI: 10.1007/s12034-019-1796-2]

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